

2MBI600VD-060-50

IGBT Modules

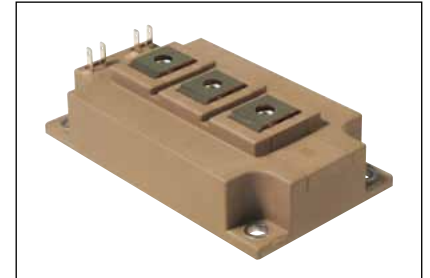
IGBT MODULE (V series) 600V / 600A / 2 in one package

■ Features

- High speed switching
- Voltage drive
- Low Inductance module structure

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial machines, such as Welding machines



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units	
Inverter	Collector-Emitter voltage	V _{CEs}	600	V	
	Gate-Emitter voltage	V _{GES}	±20	V	
	Collector current	I _c	Continuous Tc=80°C	600	
		I _c pulse	1ms Tc=80°C	1200	
		-I _c		600	
		-I _c pulse	1ms	1200	
Collector power dissipation	P _c	1 device	2940	W	
Junction temperature	T _j		175	°C	
Operating junction temperature (under switching conditions)	T _{jop}		150		
Case temperature	T _c		125		
Storage temperature	T _{stg}		-40 ~ +125		
Isolation voltage	between terminal and copper base (*1) V _{iso}	AC : 1min.	2500	VAC	
Screw torque	Mounting (*2)		6.0	N m	
	Terminals (*3)		5.0		

Note *1: All terminals should be connected together during the test.

Note *2: Recommendable Value : 3.0-6.0 Nm (M5 or M6)

Note *3: Recommendable Value : 2.5-5.0 Nm (M6)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero gate voltage collector current	I _{CEs}	V _{GE} = 0V, V _{CE} = 600V	-	-	2.0	mA	
Gate-Emitter leakage current	I _{GES}	V _{CE} = 0V, V _{GE} = ±20V	-	-	800	nA	
Gate-Emitter threshold voltage	V _{GE(th)}	V _{CE} = 20V, I _c = 600mA	6.2	6.7	7.2	V	
Collector-Emitter saturation voltage	V _{CE(sat)} (terminal)	V _{GE} = 15V I _c = 600A	Tj=25°C	-	1.85	2.30	V
			Tj=125°C	-	2.15	-	
			Tj=150°C	-	2.35	-	
	V _{CE(sat)} (chip)		Tj=25°C	-	1.60	2.05	
			Tj=125°C	-	1.90	-	
			Tj=150°C	-	2.00	-	
Internal gate resistance	R _{g(int)}	-	-	1.5	-	Ω	
Input capacitance	C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz	-	38.9	-	nF	
Turn-on time	ton	V _{CC} = 300V, I _c = 600A V _{GE} = ±15V, R _G = 2.2Ω Tj = 150°C, L _s = 30nH	-	0.75	-	μsec	
	tr		-	0.40	-		
	tr(i)		-	0.15	-		
	toff		-	0.75	-		
Turn-off time	tf	-	-	0.07	-		
Forward on voltage	V _F (terminal)	V _{GE} = 0V I _F = 600A	Tj=25°C	-	1.70	2.25	V
			Tj=125°C	-	1.60	-	
			Tj=150°C	-	1.57	-	
	V _F (chip)		Tj=25°C	-	1.60	1.85	
			Tj=125°C	-	1.50	-	
			Tj=150°C	-	1.47	-	
Reverse recovery time	trr	I _F = 600A	-	0.25	-	μsec	

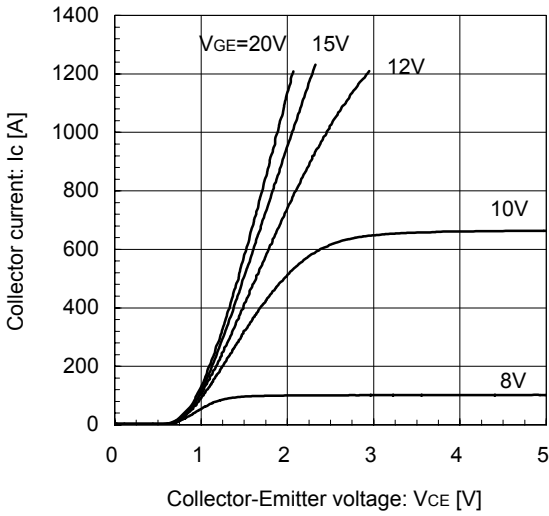
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	R _{th(j-c)}	IGBT FWD	-	-	0.051	°C/W
Contact thermal resistance (1device) (*4)	R _{th(c-f)}	with Thermal Compound	-	0.0125	-	

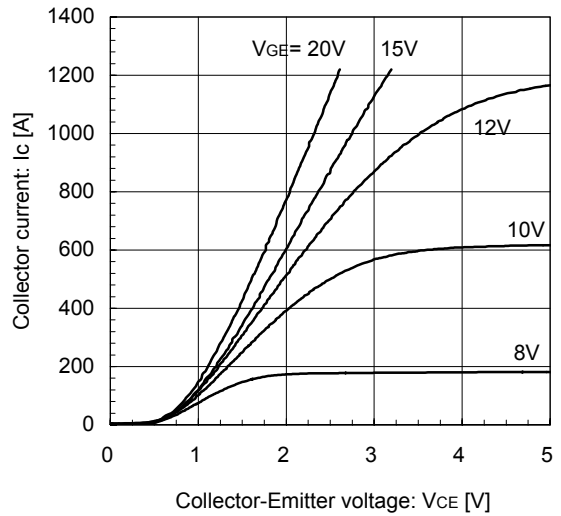
Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

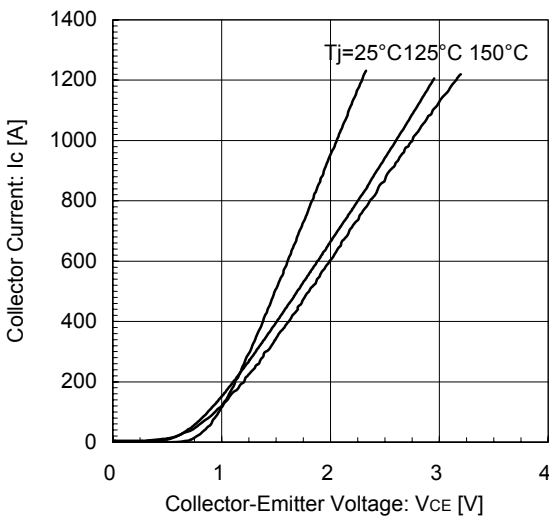
Collector current vs. Collector-Emittor voltage (typ.)
T_j = 25°C / chip



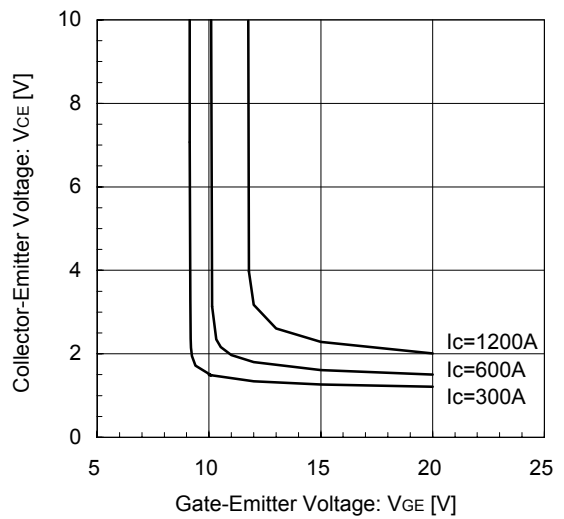
Collector current vs. Collector-Emittor voltage (typ.)
T_j = 150°C / chip



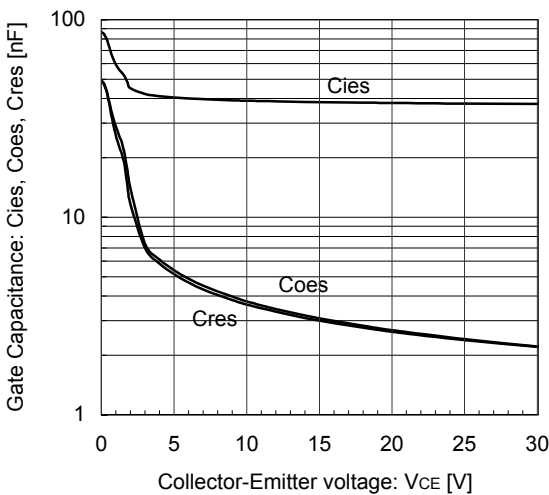
Collector current vs. Collector-Emittor voltage (typ.)
V_{GE} = 15V / chip



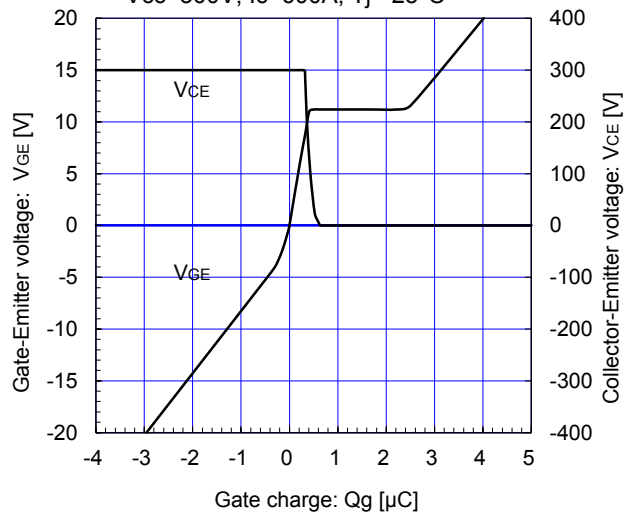
Collector-Emittor voltage vs. Gate-Emittor voltage
T_j = 25°C / chip



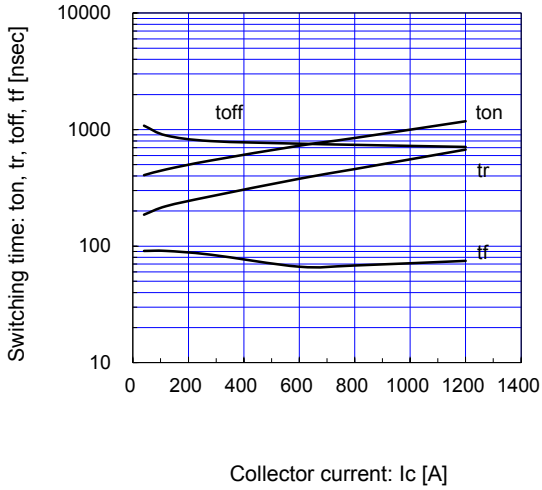
Gate Capacitance vs. Collector-Emittor Voltage
V_{GE} = 0V, f = 1MHz, T_j = 25°C



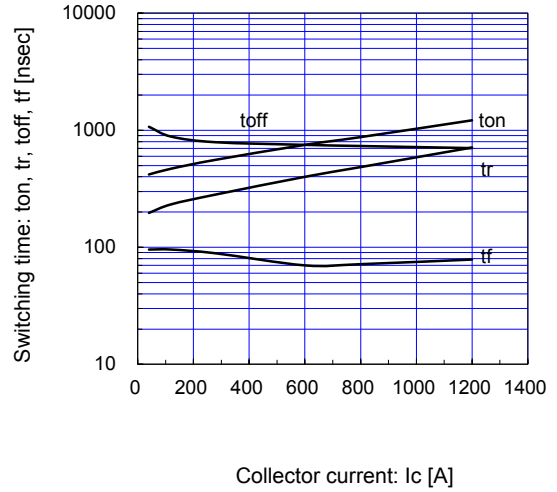
Dynamic Gate Charge (typ.)
V_{CC} = 300V, I_C = 600A, T_j = 25°C



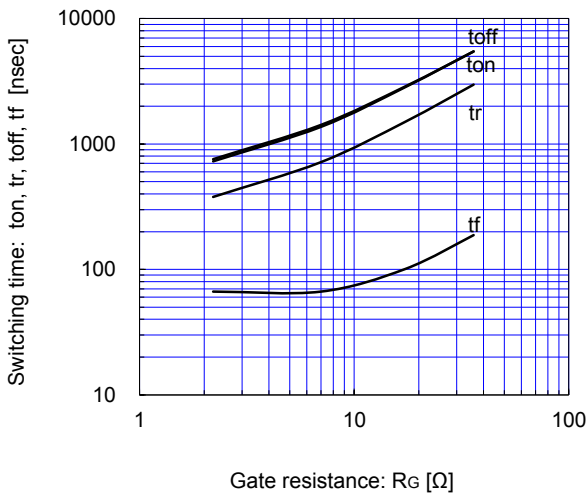
Switching time vs. Collector current (typ.)
 $V_{CC}=300V, V_{GE}=\pm 15V, R_G=2.2\Omega, T_j=125^\circ C$



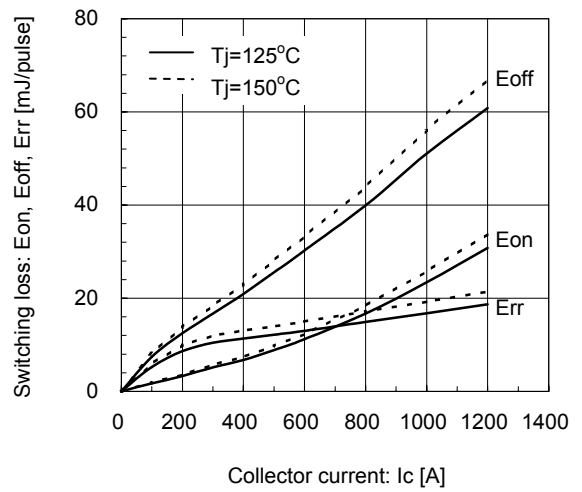
Switching time vs. Collector current (typ.)
 $V_{CC}=300V, V_{GE}=\pm 15V, R_G=2.2\Omega, T_j=150^\circ C$



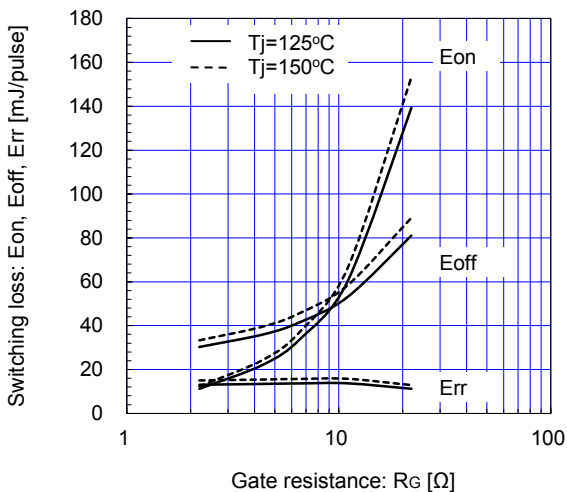
Switching time vs. Gate resistance (typ.)
 $V_{CC}=300V, I_c=600A, V_{GE}=\pm 15V, T_j=125^\circ C$



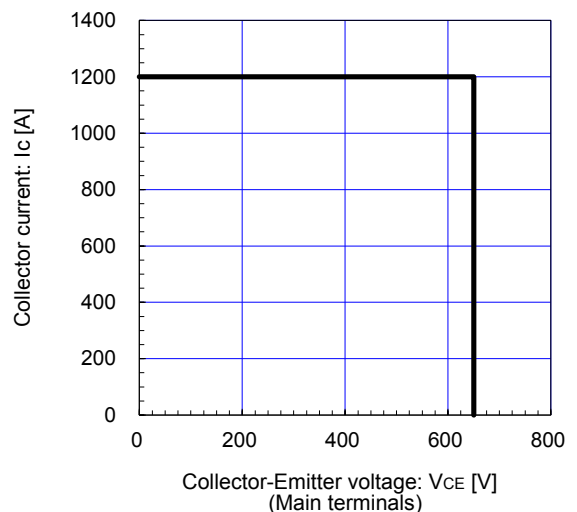
Switching loss vs. Collector current (typ.)
 $V_{CC}=300V, V_{GE}=\pm 15V, R_G=2.2\Omega, T_j=125^\circ C, 150^\circ C$



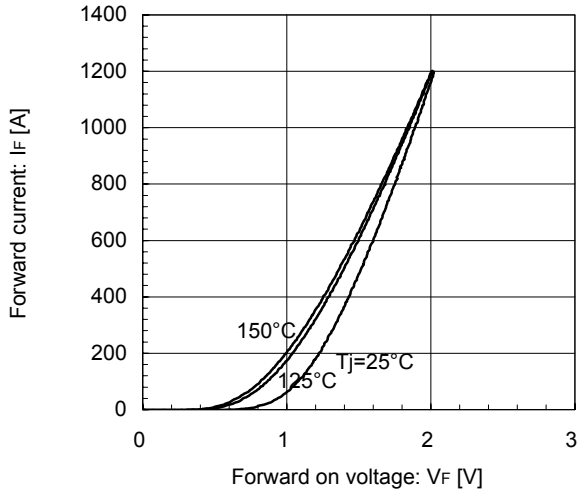
Switching loss vs. Gate resistance (typ.)
 $V_{CC}=300V, I_c=600A, V_{GE}=\pm 15V, T_j=125^\circ C, 150^\circ C$



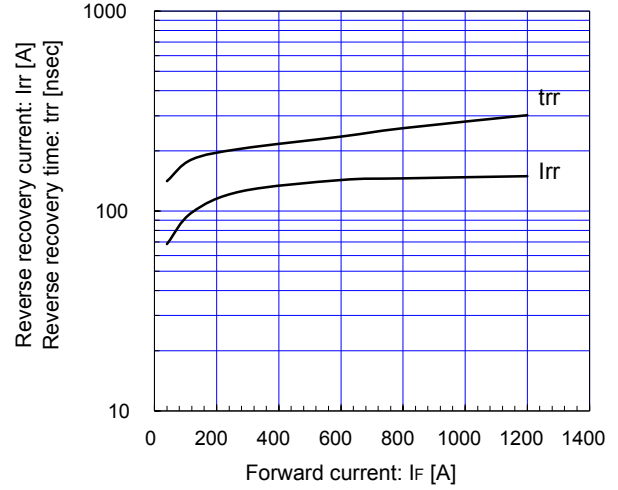
Reverse bias safe operating area (max.)
 $+V_{GE}=15V, -V_{GE}=15V, R_G=2.2\Omega, T_j=150^\circ C$



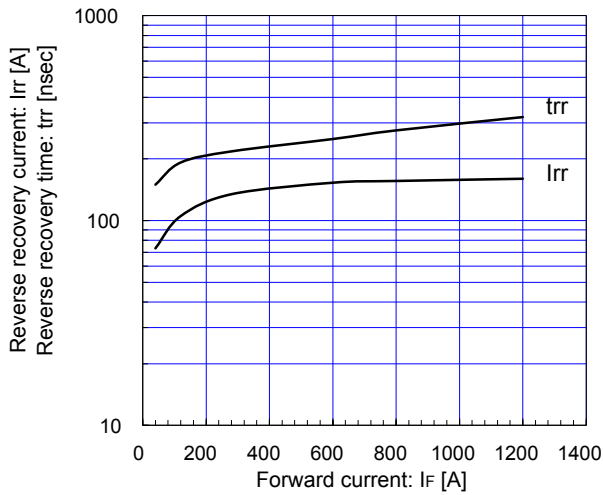
Forward Current vs. Forward Voltage (typ.)
chip



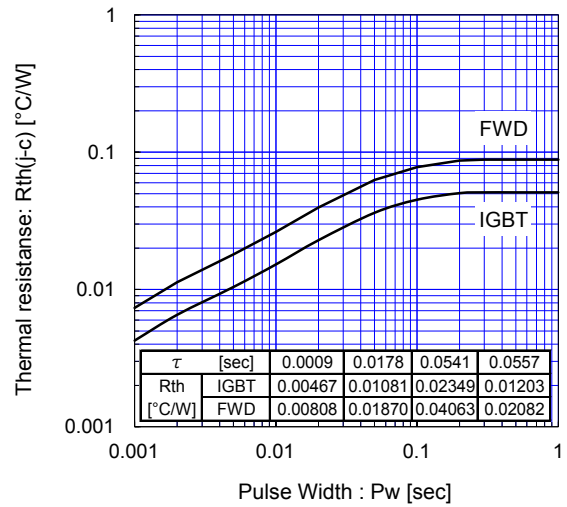
Reverse Recovery Characteristics (typ.)
Vcc=300V, VGE=±15V, RG=2.2Ω, Tj=125°C



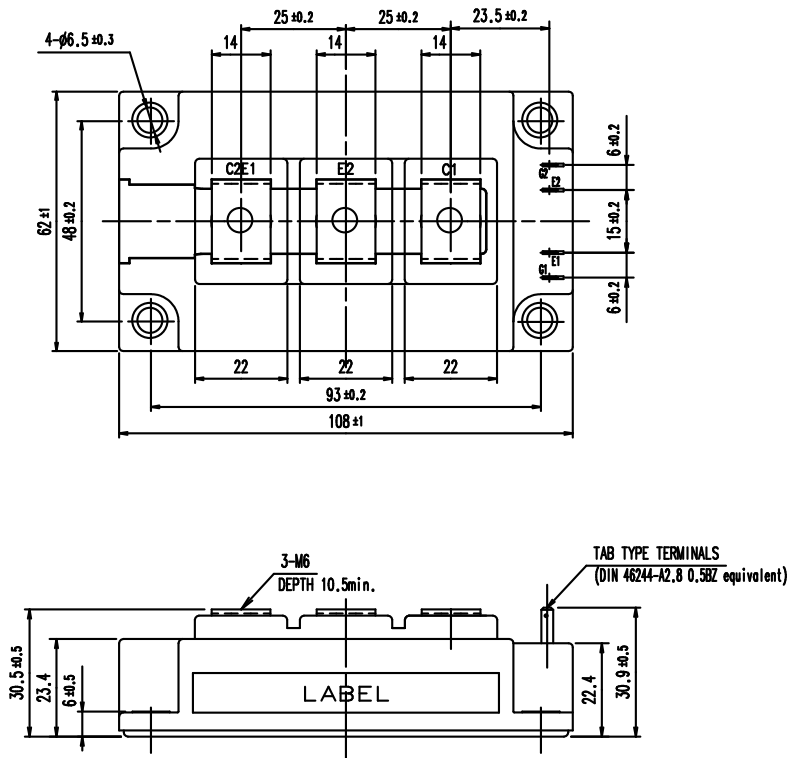
Reverse Recovery Characteristics (typ.)
Vcc=300V, VGE=±15V, RG=2.2Ω, Tj=150°C



Transient Thermal Resistance (max.)

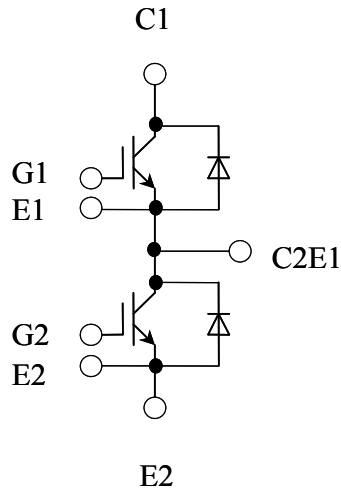


■ Outline Drawings (Unit: mm)



Weight: 370g (typ.)

■ Equivalent Circuit



WARNING

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IGBT Modules

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